

Hi-Rel NPN and PNP bipolar transistor 60 V, 2 A

Target specification

Features

Polarity	BV_{CEO}	I_C (max)	$h_{FE}^{(1)}$
NPN	60 V	0.8 A	160
PNP	-60 V	-0.8 A	160

1. @ $I_C = 1$ A and $V_{CE} = 2$ V.

- Very low collector-emitter saturation voltage
- High current gain characteristic
- Fast-switching speed: $FT = 130$ MHz
- Hermetic package
- Manufactured "according to ESCC 5000 specification"

Applications

- Power MOSFET driver

Description

The 2ST3360 power bipolar transistor is a fast dual complementary device (NPN and PNP) housed in a single LCC-6 hermetic Hi-Rel package, specifically designed for Aerospace Hi-Rel applications. Its radiation hardness allows key parameters such as gain and leakage current to stay at best in class post irradiation levels.

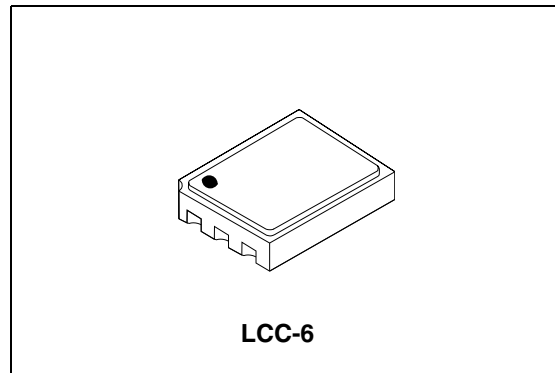
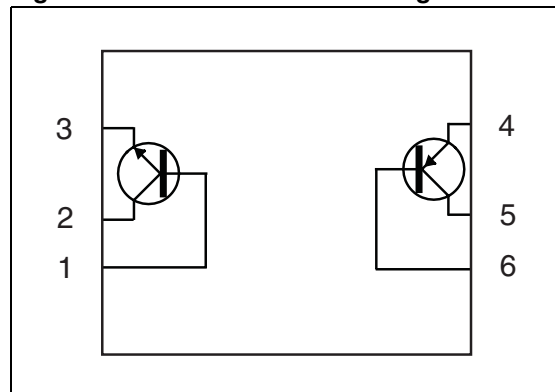


Figure 1. Internal schematic diagram



ST proprietary technology also allows a high level of electrical performances for both devices of the pair. In particular, the high switching performance of both device makes this pair ideal for applications such as power MOSFET driver.

Table 1. Device summary⁽¹⁾

Order code	ESCC part number	Quality Level	Radiation level	Package	Lead finish	Mass	EPPL
2ST3360U1	-	Engineering model	-	LCC-6	Gold	0.20 g	-

1. Contact ST sales office for information about the specific conditions for tape and reel packing.

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1 Absolute maximum ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		NPN	PNP	
V_{CBO}	Collector-base voltage ($I_E = 0$)	60	-60	V
V_{CEO}	Collector-emitter voltage ($I_B = 0$)	60	-60	V
V_{EBO}	Emitter-base voltage ($I_C = 0$)	6	-6	V
I_C	Collector current	0.8	-0.8	A
I_{CM}	Collector peak current ($t_P < 5$ ms)	4	-4	A
I_B	Base current	0.2	-0.2	A
I_{BM}	Base peak current ($t_P < 5$ ms)	0.4	-0.4	A
P_{TOT}	Total dissipation at $T_{amb} = 25$ °C	1.4		W
T_{stg}	Storage temperature	-65 to 200		°C
T_J	Max. operating junction temperature	200		°C

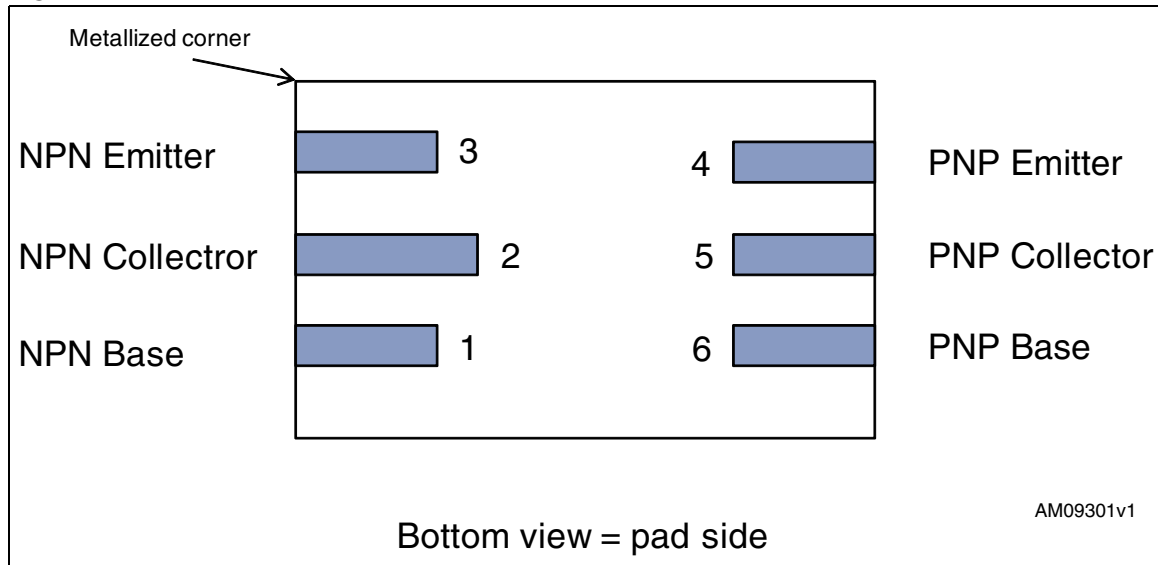
Table 3. Thermal data

Symbol	Parameter	Value	Unit
R_{thJA}	Thermal resistance junction-ambient max	125	°C/W

Note: Mounted on a 15 x 15 x 0.6 mm ceramic substrate.

2 Pin configuration

Figure 2. Pin connection



3 Electrical characteristics

$T_{CASE} = 25\text{ °C}$; unless otherwise specified.

Table 4. Electrical characteristics for NPN

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector cut-off current ($I_E = 0$)	$V_{CB} = 60\text{ V}$ $V_{CB} = 60\text{ V}, T_A = 110\text{ °C}$			100 10	nA μA
I_{EBO}	Emitter cut-off current ($I_C = 0$)	$V_{EB} = 6\text{ V}$			100	nA
$V_{BE(on)}$	Base-emitter on voltage	$V_{CE} = 2\text{ V}$ $I_C = 100\text{ mA}$		650		mV
$V_{CE(sat)}^{(1)}$	Collector-emitter saturation voltage	$I_C = 2\text{ A}$ $I_B = 100\text{ mA}$		550		mV
$h_{FE}^{(1)}$	DC current gain	$I_C = 100\text{ mA}$ $V_{CE} = 2\text{ V}$ $I_C = 1\text{ A}$ $V_{CE} = 2\text{ V}$	80 160		400	
t_d	Resistive load Delay time	$I_C = 2\text{ A}$ $V_{CC} = 10\text{ V}$ $I_{B(on)} = -I_{B(off)} = 200\text{ mA}$ $V_{BE(off)} = -5\text{ V}$		20		ns
t_r	Rise time			70		ns
t_s	Storage time			830		ns
t_f	Fall time			67		ns
f_T	Transition frequency	$I_C = 0.1\text{ A}$ $V_{CE} = 10\text{ V}$		130		MHz

1. Pulse test: pulse duration $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$

Table 5. Electrical characteristics for PNP⁽¹⁾

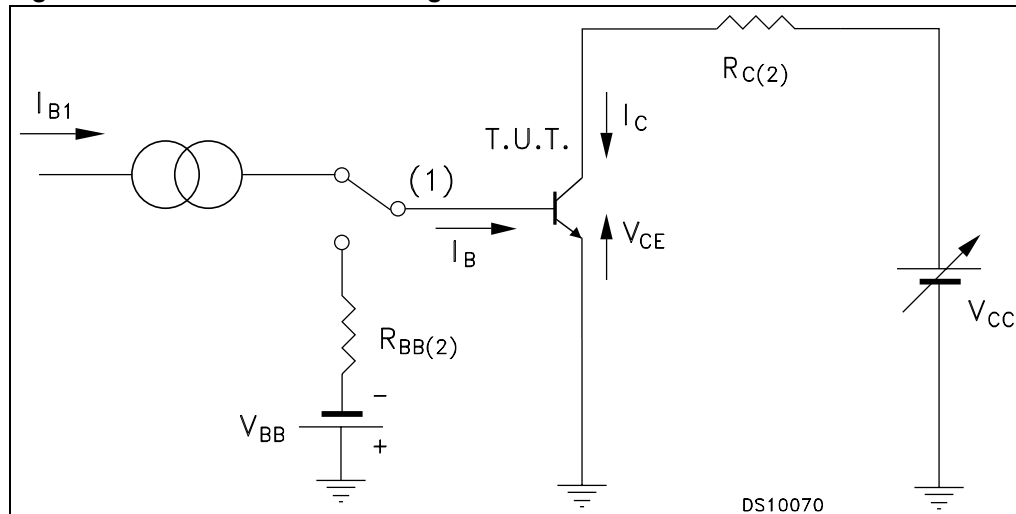
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector cut-off current ($I_E = 0$)	$V_{CB} = 60\text{ V}$ $V_{CB} = 60\text{ V}, T_A = 110\text{ °C}$			100 10	nA μA
I_{EBO}	Emitter cut-off current ($I_C = 0$)	$V_{EB} = 6\text{ V}$			100	nA
$V_{BE(on)}$	Base-emitter on voltage	$V_{CE} = 2\text{ V}$ $I_C = 100\text{ mA}$		650		mV
$V_{CE(sat)}^{(2)}$	Collector-emitter saturation voltage	$I_C = 2\text{ A}$ $I_B = 100\text{ mA}$		550		mV
$h_{FE}^{(1)}$	DC current gain	$I_C = 100\text{ mA}$ $V_{CE} = 2\text{ V}$ $I_C = 1\text{ A}$ $V_{CE} = 2\text{ V}$	80 160		400	
t_d	Resistive load Delay time	$I_C = 2\text{ A}$ $V_{CC} = 10\text{ V}$ $I_{B(on)} = -I_{B(off)} = 200\text{ mA}$ $V_{BE(off)} = -5\text{ V}$		22		ns
t_r	Rise time			54		ns
t_s	Storage time			360		ns
t_f	Fall time			42		ns
f_T	Transition frequency	$I_C = 0.1\text{ A}$ $V_{CE} = 10\text{ V}$		130		MHz

1. For PNP type voltage and current values are negative.

2. Pulse test: pulse duration $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$

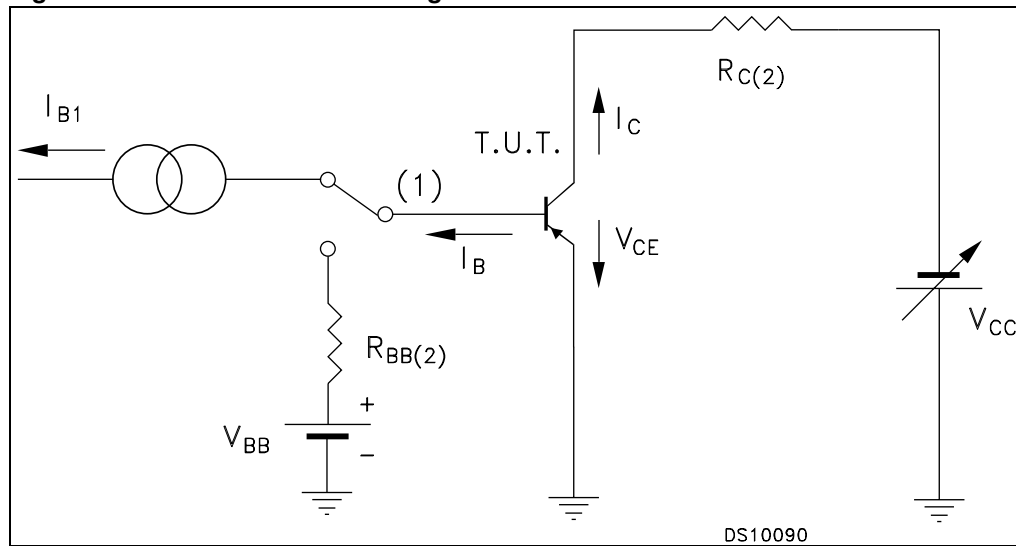
3.1 Test circuits

Figure 3. Resistive load switching for NPN



1. Fast electronic switch.
2. Non-inductive resistor.

Figure 4. Resistive load switching for PNP



1. Fast electronic switch.
2. Non-inductive resistor.

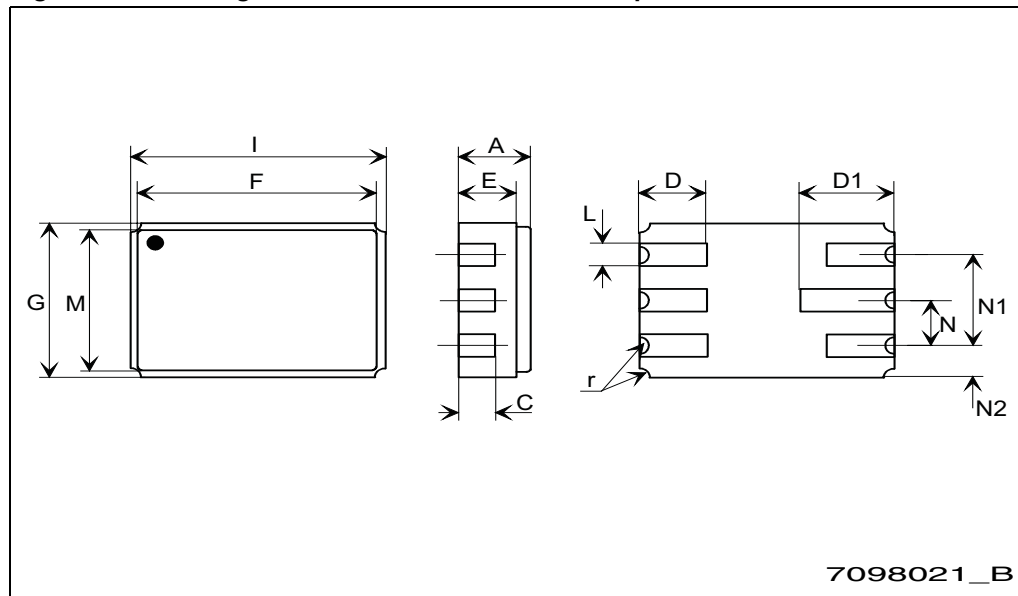
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Table 6. Ceramic leadless chip carrier 6 mechanical data

Dim.	mm.			inch.		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	1.53		1.96	.060		.077
C	0.78	0.89	0.99	.031	.035	.039
D	1.52	1.65	1.78	.060	.065	.070
E	1.24	1.40	1.55	.049	.055	.059
F	5.77	5.84	5.92	.227	.230	.233
G	4.19	4.31	4.45	.165	.170	.175
I	6.10	6.22	6.35	.240	.245	.250
L	0.56	0.63	0.71	.022	.025	.028
M	3.86	3.94	4.01	.152	.155	.158
N	1.14	1.27	1.40	.045	.050	.055
N1	2.41	2.54	2.67	.095	.100	.105
N2	0.64	0.89	1.14	.025	.035	.045
r		0.23			.009	
D1	2.08	2.28	2.49	.082	.090	.098

Figure 5. Drawing dimension ceramic leadless chip carrier 6



5 Order code

Table 7. Ordering information⁽¹⁾

Order code	ESCC part number	Quality level	Radiation level	Package	Lead finish	Marking	EPPL	Packing
2ST3360U1	-	Engineering model	-	LCC-6	Gold	2ST3360U1	-	Wafflepack

1. Contact ST sales office for information about the specific conditions for tape and reel packing.

6 Revision history

Table 8. Document revision history

Date	Revision	Changes
18-Jul-2011	1	Initial release.

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